

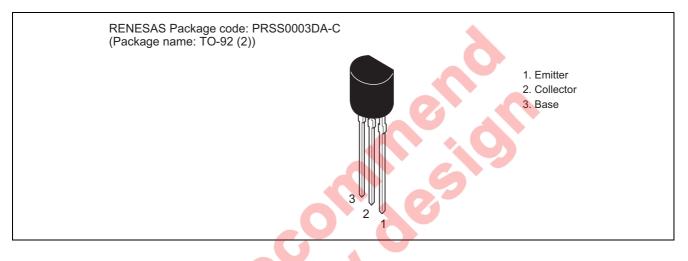
2SC535 Silicon NPN Epitaxial Planar

REJ03G0683-0200 (Previous ADE-208-1047) Rev.2.00 Aug.10.2005

Application

VHF amplifier, mixer, local oscillator

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	30	V
Collector to emitter voltage	V _{CEO}	20	V
Emitter to base voltage	V _{EBO}	4	V
Collector current	Ι _C	20	mA
Collector power dissipation	Pc	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

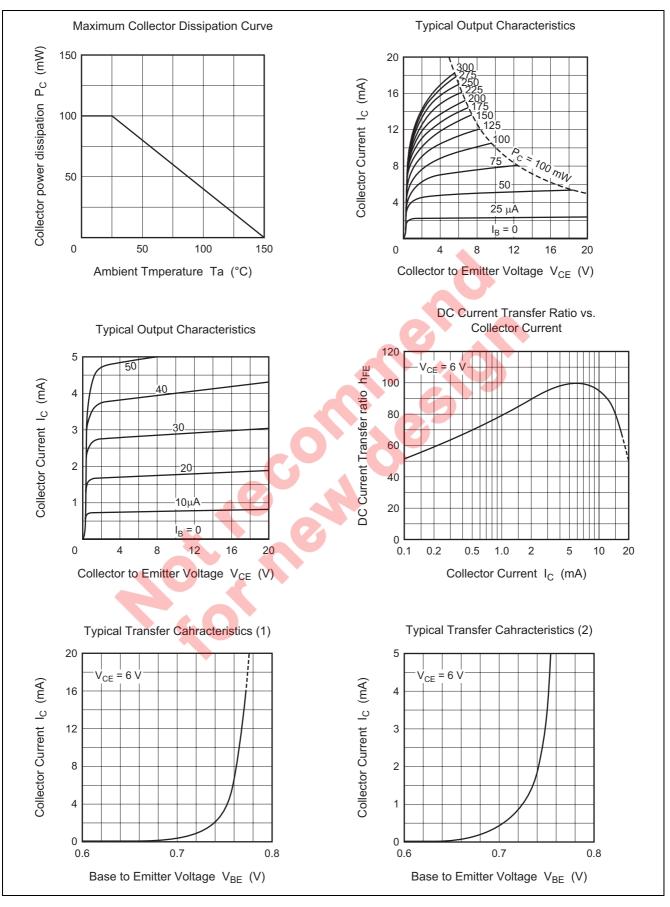


Electrical Characteristics

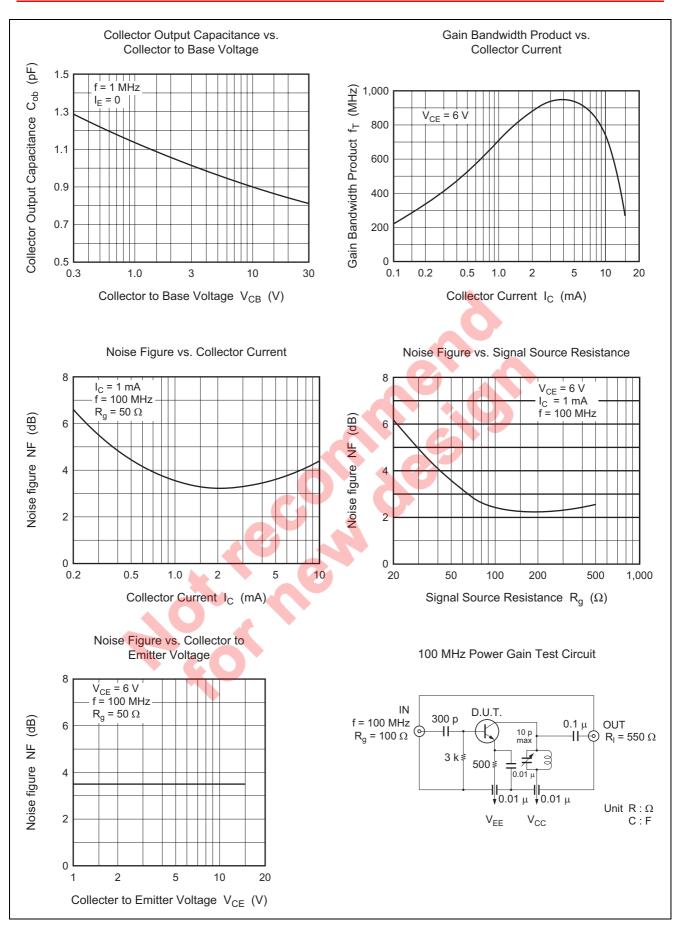
Collector to base breakdown voltage $V_{(BR)CBO}$ 30VI_C = 10 μ A, I_E =Collector to emitter breakdown voltage $V_{(BR)CEO}$ 20VI_C = 1 mA, R_BEEmitter to base breakdown voltage $V_{(BR)CEO}$ 20VI_C = 1 mA, R_BECollector cutoff currentI_CBOVI_E = 10 μ A, I_E =Collector cutoff currentI_CBO0.5 μ A $V_{CB} = 10 V, I_E =$ DC current transfer ratiohFE*160200V_{CE} = 6 V, I_C = 1Base to emitter voltageVBE0.72VV_CE = 6 V, I_C = 1Collector to emitter saturation voltage $V_{CE(sat)}$ 0.17VI_C = 20 mA, I_B =Gain bandwidth productfr450940MHzV_{CE} = 6 V, I_C = 1Collector output capacitanceCob0.91.2pF $V_{CB} = 10 V, I_E =$ Power gainPG1720dB $V_{CE} = 6 V, I_C = 1$ Input admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 V, I_C = 1$ Reverse transfer admittance (typ)yie0.08 + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows0.08 + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows	= ∞ = 0 1 mA 1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, g = 50 Ω
Collector to emitter breakdown voltageV(BR)CEO20VIc = 1 mA, RBE :Emitter to base breakdown voltage $V_{(BR)CEO}$ 4VIe = 10 μ A, Ic =Collector cutoff currentICBO0.5 μ A $V_{CB} = 10 V$, Ie =DC current transfer ratiohFE*160200 $V_{CE} = 6 V$, Ic =Base to emitter voltage V_{BE} 0.72V $V_{CE} = 6 V$, Ic =Collector to emitter saturation voltage V_{BE} 0.17VIc = 20 mA, IB =Gain bandwidth productfT450940MHz $V_{CE} = 6 V$, Ic =1CCollector output capacitanceCob0.91.2pF $V_{CE} = 6 V$, Ic =1CPower gainPG1720dB $V_{CE} = 6 V$, Ic =1E100 MHzNoise figureNF3.55.5dB $V_{CE} = 6 V$, Ic =1E100 MHz, RgInput admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 V$, Ic =100 MHz, RgNote:1. The 2SC535 is grouped by hFE as follows.mSNote + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows0.08 + j0.82mS	= ∞ = 0 1 mA 1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, g = 50 Ω
Emitter to base breakdown voltage $V_{(BR)EBO}$ 4VIE = 10 μ A, Ic =Collector cutoff currentIcBO0.5 μ AVcB = 10 V, IE =DC current transfer ratiohFE*160200VcE = 6 V, Ic = 10 PA, Ic =Base to emitter voltageVBE0.72VVcE = 6 V, Ic = 10 PA, Ic =Collector to emitter saturation voltageVBE0.72VVcE = 6 V, Ic = 10 PA, Ic	= 0 = 0 1 mA 1 mA = 4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, $g_g = 50$ Ω
Collector cutoff currentIcBO0.5 μ AVcB = 10 V, IE =DC current transfer ratiohFE*160200VcE = 6 V, Ic = 10 V, IE =Base to emitter voltageVBE0.72VVcE = 6 V, Ic = 10 V, IE =Base to emitter voltageVBE0.72VVcE = 6 V, Ic = 10 V, IE =Collector to emitter saturation voltageVCE(sat)0.17VIc = 20 mA, IB =Gain bandwidth productfT450940MHzVcE = 6 V, Ic = 10 V, IE =Collector output capacitanceCob0.91.2pFVcB = 10 V, IE =Power gainPG1720dBVcE = 6 V, Ic = 10 HzNoise figureNF3.55.5dBVcE = 6 V, Ic = 10 HzInput admittance (typ)yie1.3 + j5.3mSVcE = 6 V, Ic = 10 Hz, Reverse transfer admittance (typ)Yee-0.078 - j0.41mSForward transfer admittance (typ)yie32 - j10mSNote:1. The 2SC535 is grouped by hFE as follows.mSNFE as follows.BC60 to 120100 to 200100 to 200100 to 200	= 0 1 mA 1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, $g_{g} = 50 \Omega$
DC current transfer ratio h_{FE}^{*1} 60200 $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ M}$ Base to emitter voltage V_{BE} 0.72 V $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ M}$ Collector to emitter saturation voltage $V_{CE(sat)}$ 0.17 V $I_C = 20 \text{ mA}, I_B = 10 \text{ M}$ Gain bandwidth product f_T 450 940 MHz $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ M}$ $I_E = 20 \text{ mA}, I_B = 10 \text{ Collector output capacitance}$ Collector output capacitanceCob 0.9 1.2 pF $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ MHz}$ Power gainPG 17 20 dB $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ MHz}$ Noise figureNF 3.5 5.5 dB $V_{CE} = 6 \text{ V}, \text{ Ic} = 100 \text{ MHz}$ Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6 \text{ V}, \text{ Ic} = 100 \text{ MHz}$ Forward transfer admittance (typ)yife $32 - j10$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by h_{FE} as follows.mS	1 mA 1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, $g_{g} = 50 \Omega$
Base to emitter voltage V_{BE} 0.72 V $V_{CE} = 6$ $V, I_{C} = 20$ $M, I_{B} = 10$ Collector to emitter saturation voltage f_T 450940MHz $V_{CE} = 6$ $V, I_{C} = 30$ Gain bandwidth product f_T 450940MHz $V_{CE} = 6$ $V, I_{C} = 30$ Collector output capacitanceCob 0.9 1.2 pF $V_{CE} = 6$ $V, I_{E} = 30$ Power gainPG1720dB $V_{CE} = 6$ $V, I_{E} = 30$ Noise figureNF 3.5 5.5 dB $V_{CE} = 6$ $V, I_{E} = 30$ Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6$ $V, I_{E} = 30$ Reverse transfer admittance (typ)yfe $32 - j10$ mS $V_{CE} = 6$ $V, I_{E} = 30$ Output admittance (typ)yfe $32 - j10$ mS MHz $V_{CE} = 6$ $V, I_{E} = 30$ Note:1. The 2SC535 is grouped by h_{FE} as follows. MS MS MS MS Mote:1. The 2SC535 is grouped by h_{FE} as follows. MS MS MS MS	1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, $g_{g} = 50 \Omega$
Collector to emitter saturation voltage $V_{CE(sat)}$ - 0.17 -V $I_C = 20 \text{ mA}, I_B = 3$ Gain bandwidth product f_T 450940-MHz $V_{CE} = 6 \text{ V}, I_C = 3$ Collector output capacitanceCob- 0.9 1.2 pF $V_{CB} = 10 \text{ V}, I_E = 3$ Power gainPG1720-dB $V_{CE} = 6 \text{ V}, I_C = 3$ Noise figureNF- 3.5 5.5 dB $V_{CE} = 6 \text{ V}, I_C = 3$ Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6 \text{ V}, I_C = 3$ Reverse transfer admittance (typ)yfe $32 - j10$ mS $V_{CE} = 6 \text{ V}, I_C = 3$ Output admittance (typ)yfe $32 - j10$ mS $V_{CE} = 6 \text{ V}, I_C = 3$ Note:1. The 2SC535 is grouped by h _{FE} as follows.mSmS MS	=4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, g _g = 50 Ω
Gain bandwidth product f_T 450940—MHz $V_{CE} = 6 \text{ V}, I_C = 5$ Collector output capacitanceCob—0.91.2pF $V_{CB} = 10 \text{ V}, I_E = 5$ Power gainPG1720—dB $V_{CE} = 6 \text{ V}, I_C = 5$ Noise figureNF—3.55.5dB $V_{CE} = 6 \text{ V}, I_C = 5$ Input admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 \text{ V}, I_C = 5$ Reverse transfer admittance (typ)yre $-0.078 - j0.41$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by h _{FE} as follows.mSBC60 to 120100 to 200 $100 \text{ to } 200$	5 mA = 0, f = 1 MHz 1 mA, 1 mA, g _g = 50 Ω
Collector output capacitanceCob0.91.2pF $V_{CB} = 10 \text{ V}, I_E = 10 \text{ PG}$ Power gainPG1720dB $V_{CE} = 6 \text{ V}, I_C = 10 \text{ PG}$ Noise figureNF3.55.5dB $V_{CE} = 6 \text{ V}, I_C = 10 \text{ PG}$ Noise figureNF3.55.5dB $V_{CE} = 6 \text{ V}, I_C = 10 \text{ PG}$ Input admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 \text{ V}, I_C = 10 \text{ PG}$ Reverse transfer admittance (typ)yie-0.078 - j0.41mSForward transfer admittance (typ)yfe32 - j10mSOutput admittance (typ)yoe0.08 + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows.mSBC60 to 120100 to 200100 to 200	= 0, f = 1 MHz 1 mA, 1 mA, $g_{g} = 50 \Omega$
Power gainPG1720dB $V_{CE} = 6 \text{ V}, \text{ Ic} = 7$ f = 100 MHzNoise figureNF3.55.5dB $V_{CE} = 6 \text{ V}, \text{ Ic} = 7$ f = 100 MHz, RgInput admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 \text{ V}, \text{ Ic} = 7$ f = 100 MHz, RgReverse transfer admittance (typ)yre-0.078 - j0.41mSForward transfer admittance (typ)yfe32 - j10mSOutput admittance (typ)yoe0.08 + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows.BC60 to 120100 to 200	1 mA, 1 mA, g = 50 Ω
Noise figureNF- 3.5 5.5 dB $V_{CE} = 6$ V, $I_C = 7$ Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6$ V, $I_C = 7$ Reverse transfer admittance (typ)yre $-0.078 - j0.41$ mSForward transfer admittance (typ)yfe $32 - j10$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by h _{FE} as follows. mS	1 mA, g = 50 Ω
Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6 V, I_C = 100 \text{ MHz}, R_s$ Reverse transfer admittance (typ)yre $-0.078 - j0.41$ mSForward transfer admittance (typ)yfe $32 - j10$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by hFE as follows.BC60 to 120100 to 200	_g = 50 Ω
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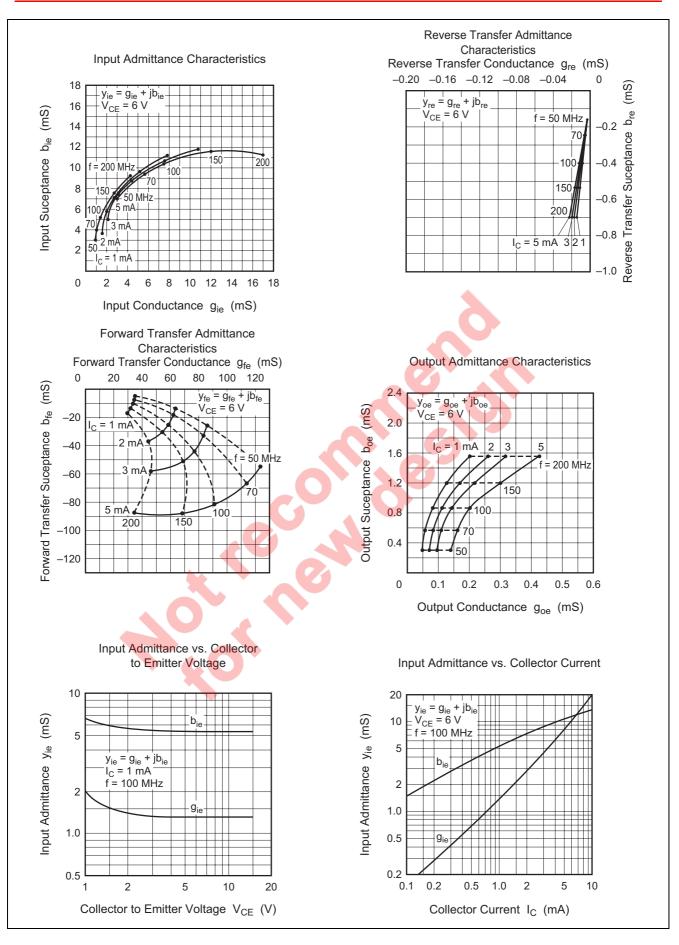


Main Characteristics

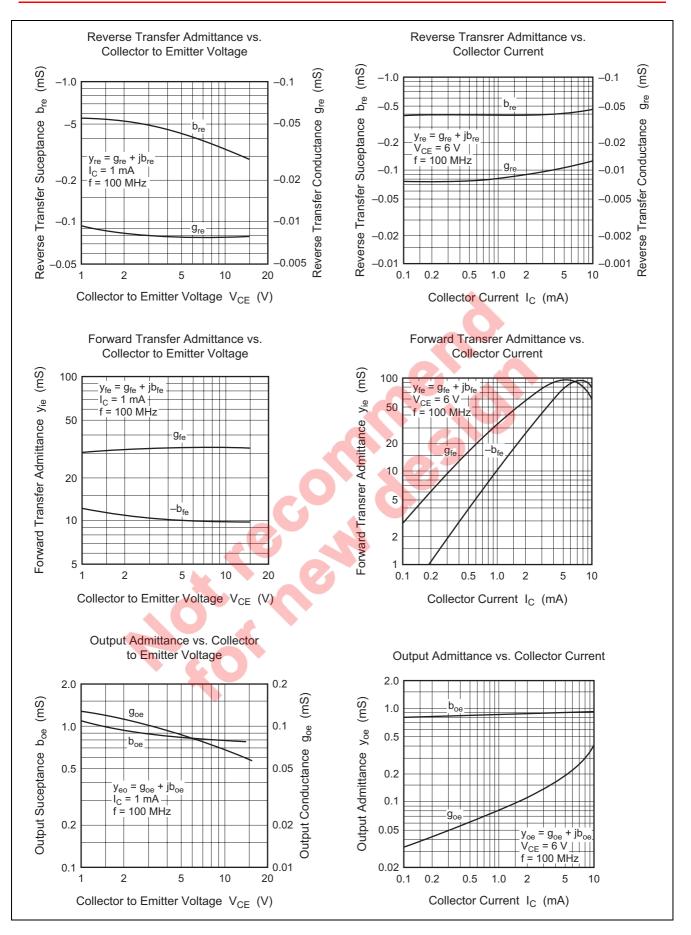






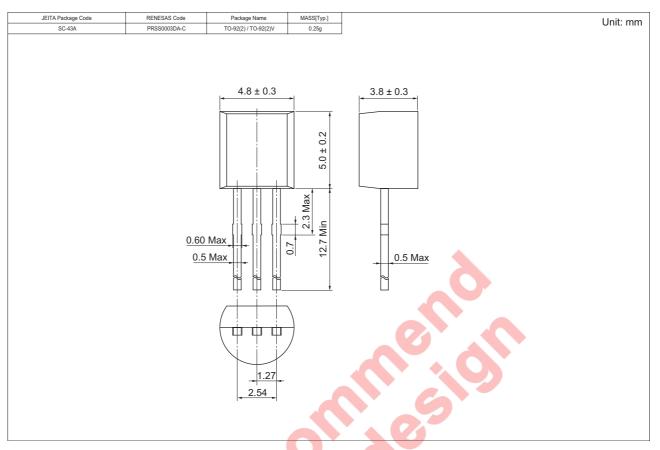








Package Dimensions



Ordering Information

Part Name	Quan	tity	Shipping Container
2SC535BTZ	2500	Ho	ld Box, Radial Taping
2SC535CTZ			

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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